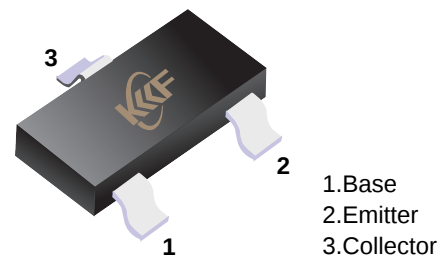


2SC2412

■ NPN Transistors

■ Features

- Low Cob.Cob=2.0pF (Typ.)



■ Simplified outline(SOT-23)

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	60	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EB0}	7	V
Collector current	I _C	0.15	A
Collector power dissipation	P _C	0.2	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

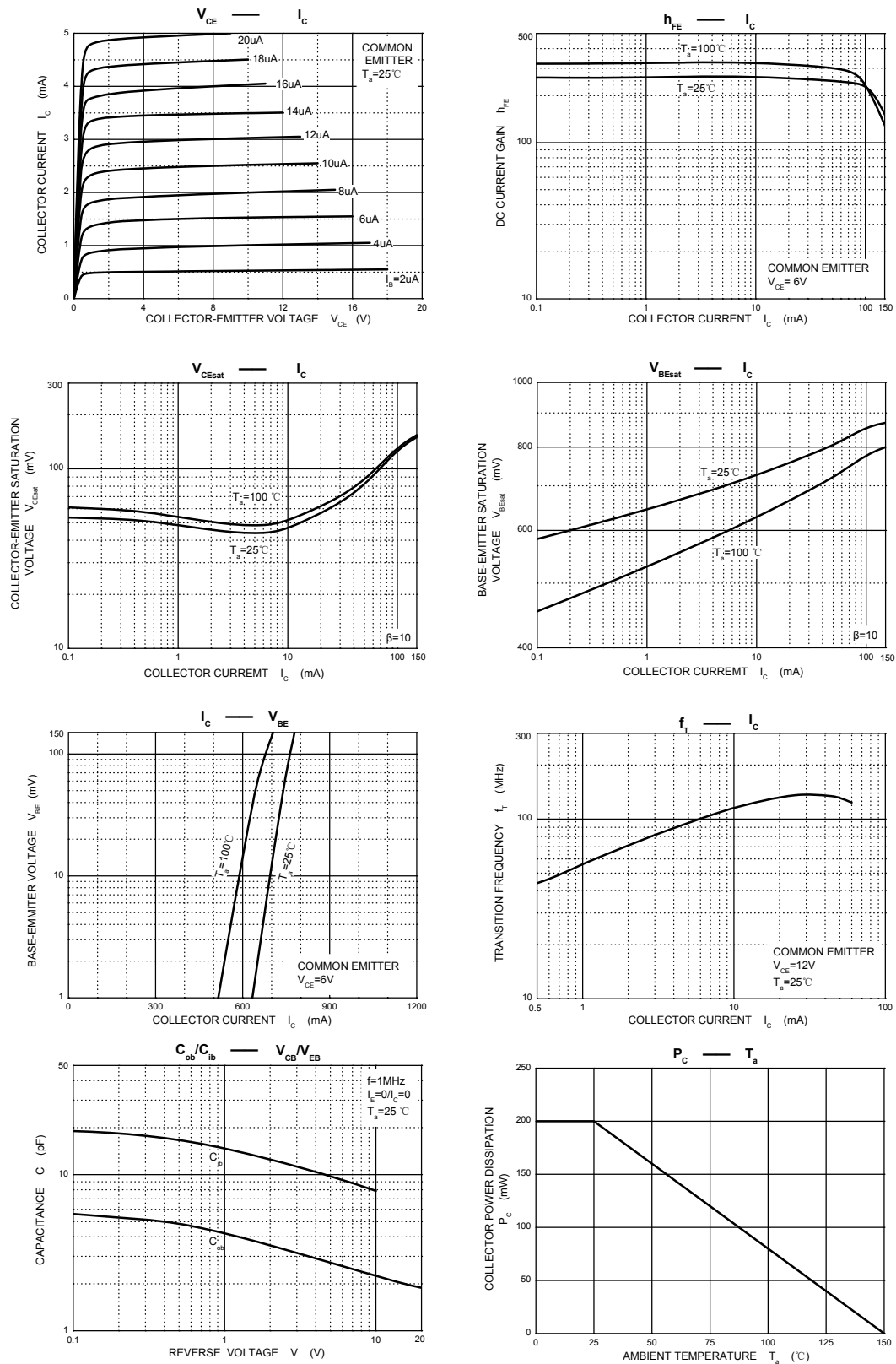
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = 50 μA, I _E = 0	60			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = 1 mA, I _B = 0	50			
Emitter - base breakdown voltage	V _{EB0}	I _E = 50 μA, I _C = 0	7			
Collector-base cut-off current	I _{CB0}	V _{CB} = 60 V, I _E = 0			100	nA
Emitter cut-off current	I _{EB0}	V _{EB} = 7V, I _C =0			100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =50 mA, I _B =5mA			0.4	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =50 mA, I _B =5mA			1.2	
DC current gain	h _{FE}	V _{CE} = 6V, I _C = 1mA	120		560	
Collector output capacitance	C _{ob}	V _{CB} = 12V, I _E = 0, f=1MHz		2	3.5	pF
Transition frequency	f _T	V _{CE} = 12V, I _E = -2mA, f=100MHz	80			MHz

■ hFE Classification

Type	2SC2412/K-Q	2SC2412/K-R	2SC2412/K-S
Range	120-270	180-390	270-560
Marking	BQ	BR	BS

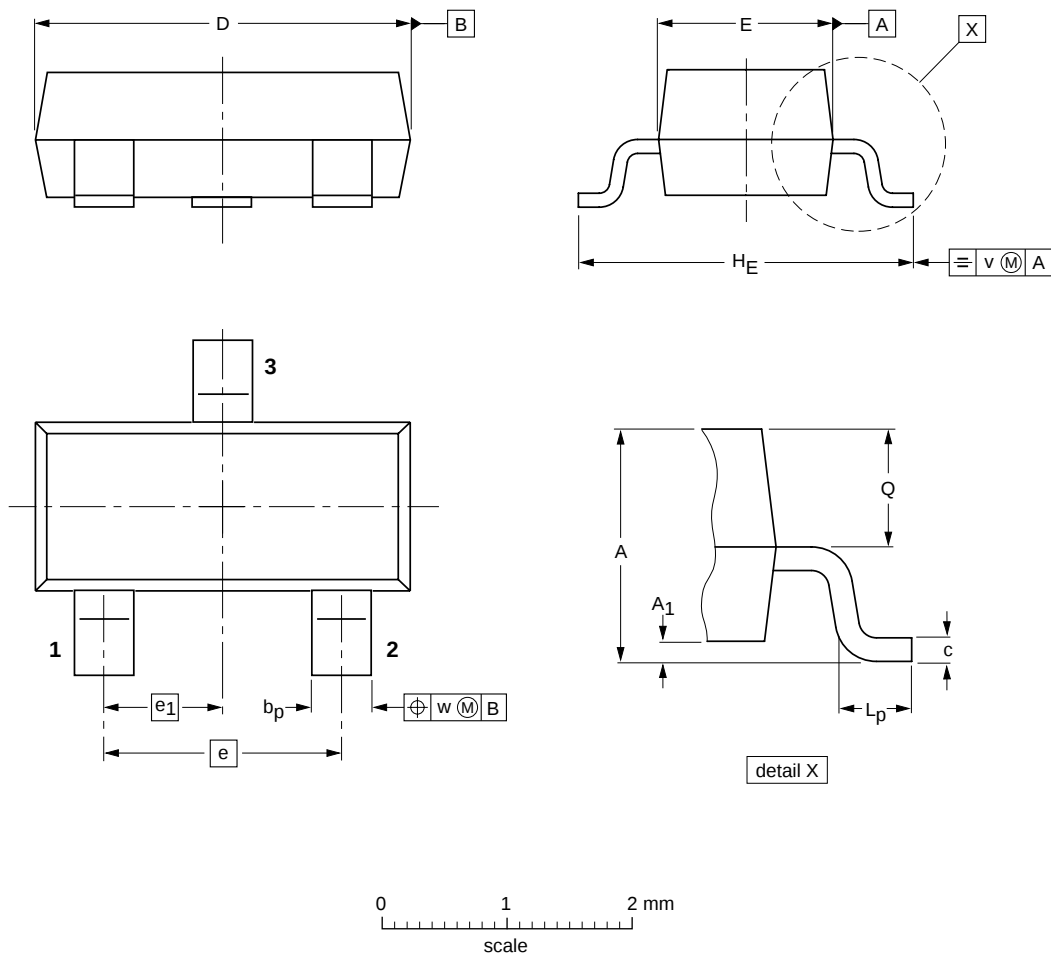
2SC2412

■ Typical Characteristics



2SC2412

■ SOT-23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1